

Gate-Tunable and Multidirection-Switchable Memristive Ferroelectric

Advanced Materials

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Electric and Light Dual-Gate Tunable MoS ₂ Memtransistor. ACS Applied Materials & Interfaces, 2019, 11, 43344-43350.	4.0	51
2	A Novel Scalable Energy-Efficient Synaptic Device: Crossbar Ferroelectric Semiconductor Junction. , 2019, , .		15
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5	The rise of 2D dielectrics/ferroelectrics. APL Materials, 2019, 7, .	2.2	66
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12	Two-dimensional materials for next-generation computing technologies. Nature Nanotechnology, 2020, 15, 545-557.	15.6	521
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18	In-plane ferroelectricity in few-layered GeS and its van der Waals ferroelectric diodes. Nanoscale, 2021, 13, 16122-16130.	2.8	15

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20	Two-dimensional ferroelectric channel transistors integrating ultra-fast memory and neural computing. <i>Nature Communications</i> , 2021, 12, 53.	5.8	160
21	Layer-dependent ferroelectricity in 2H-stacked few-layer In_2Se_3 . <i>Materials Horizons</i> , 2021, 8, 1472-1480.	6.4	37
22	Intrinsic memristive mechanisms in 2D layered materials for high-performance memory. <i>Journal of Applied Physics</i> , 2021, 129, .	1.1	15
23	Review on Recent Developments in 2D Ferroelectrics: Theories and Applications. <i>Advanced Materials</i> , 2021, 33, e2005098.	11.1	148
24	Intrinsic polarization coupling in 2D In_2Se_3 toward artificial synapse with multimode operations. <i>SmartMat</i> , 2021, 2, 88-98.	6.4	81
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26	Asymmetric Metal/ In_2Se_3 /Si Crossbar Ferroelectric Semiconductor Junction. <i>ACS Nano</i> , 2021, 15, 5689-5695.	7.3	36
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